

Complementary (N- and P-Channel) MOSFET

PRODUCT SUMMARY			
	V _{DS} (V)	R _{DS(on)} (Ω)	I _D (A)
N-Channel	30	0.018 at V _{GS} = 10 V	8.8
		0.027 at V _{GS} = 4.5 V	7.0
P-Channel	- 8	0.042 at V _{GS} = - 4.5 V	- 5.7
		0.060 at V _{GS} = - 2.5 V	- 4.8

FEATURES

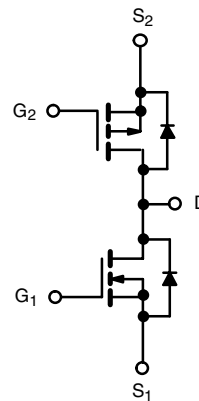
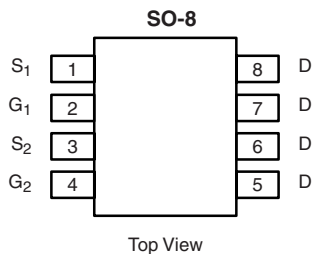
- Halogen-free According to IEC 61249-2-21 Definition
- TrenchFET® Power MOSFET
- Compliant to RoHS Directive 2002/95/EC



RoHS
COMPLIANT
HALOGEN
FREE
Available

APPLICATIONS

- Level Shift
- Load Switch



Ordering Information: Si4501ADY-T1-E3 (Lead (Pb)-free)
Si4501ADY-T1-GE3 (Lead (Pb)-free and Halogen-free)

ABSOLUTE MAXIMUM RATINGS T _A = 25 °C, unless otherwise noted							
Parameter	Symbol	N-Channel		P-Channel		Unit	
		10 s	Steady State	10 s	Steady State		
Drain-Source Voltage	V _{DS}	30		- 8		V	
Gate-Source Voltage	V _{GS}	± 20		± 8			
Continuous Drain Current (T _J = 150 °C) ^{a, b}	I _D	T _A = 25 °C	8.8	6.3	- 5.7	- 4.1	A
		T _A = 70 °C	7	5.2	- 4.5	- 3.3	
Pulsed Drain Current	I _{DM}	30		- 30		A	
Continuous Source Current (Diode Conduction) ^{a, b}	I _S	1.8	1.0	- 1.8	- 1.0		
Maximum Power Dissipation ^{a, b}	P _D	T _A = 25 °C	2.5	1.3	2.5	1.3	W
		T _A = 70 °C	1.6	0.84	1.6	0.84	
Operating Junction and Storage Temperature Range	T _J , T _{stg}	- 55 to 150				°C	

THERMAL RESISTANCE RATINGS							
Parameter	Symbol	N-Channel		P-Channel		Unit	
		Typ.	Max.	Typ.	Max.		
Maximum Junction-to-Ambient ^a	R _{thJA}	t ≤ 10 s	40	50	42	50	°C/W
		Steady State	75	95	76	95	
Maximum Junction-to-Foot (Drain)	R _{thJF}	18	23	21	26		

Notes:

a. Surface Mounted on FR4 board.

b. t ≤ 10 s.

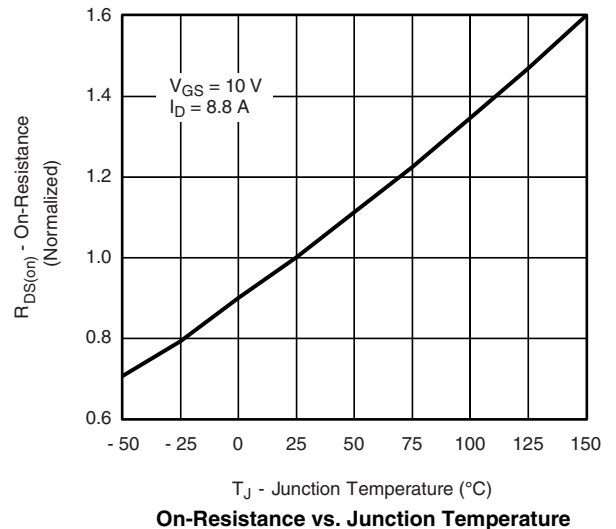
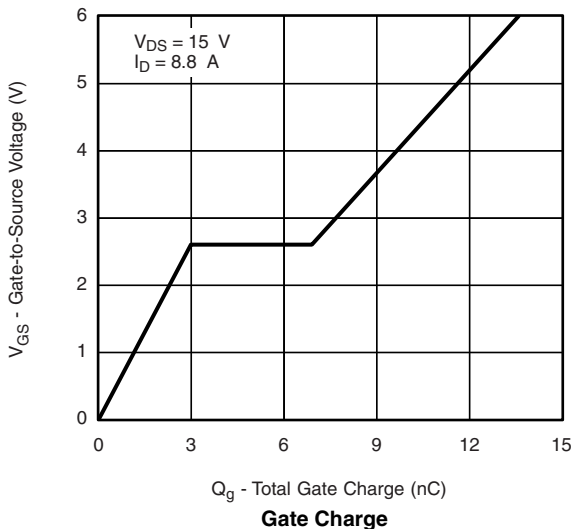
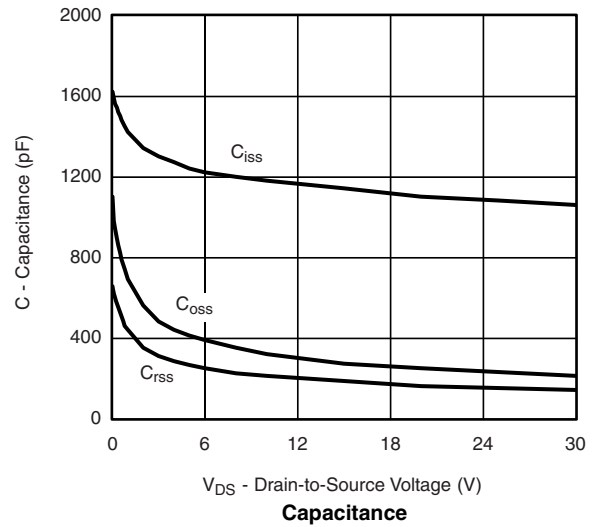
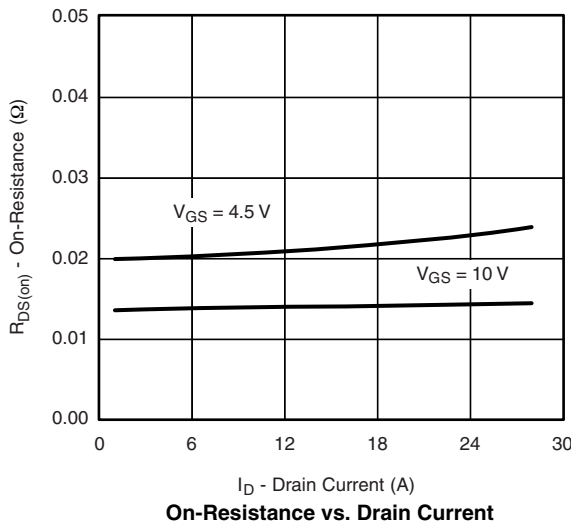
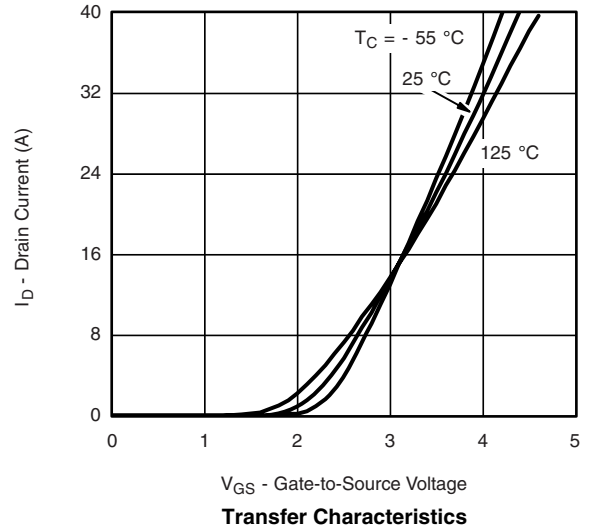
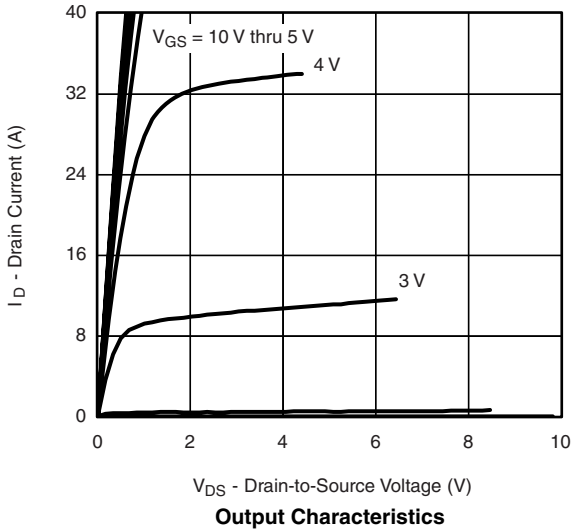
SPECIFICATIONS $T_J = 25\text{ }^\circ\text{C}$, unless otherwise noted								
Parameter	Symbol	Test Conditions		Min.	Typ. ^a	Max.	Unit	
Static								
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}, I_D = 250\text{ }\mu\text{A}$	N-Ch	0.8		1.8	V	
		$V_{DS} = V_{GS}, I_D = -250\text{ }\mu\text{A}$	P-Ch	-0.45		-1.0		
Gate-Body Leakage	I_{GSS}	$V_{DS} = 0\text{ V}, V_{GS} = \pm 20\text{ V}$	N-Ch			± 100	nA	
		$V_{DS} = 0\text{ V}, V_{GS} = \pm 8\text{ V}$	P-Ch			± 100		
Zero Gate Voltage Drain Current	I_{DSS}	$V_{DS} = 30\text{ V}, V_{GS} = 0\text{ V}$	N-Ch			1	μA	
		$V_{DS} = -8\text{ V}, V_{GS} = 0\text{ V}$	P-Ch			-1		
		$V_{DS} = 30\text{ V}, V_{GS} = 0\text{ V}, T_J = 55\text{ }^\circ\text{C}$	N-Ch			5		
		$V_{DS} = -8\text{ V}, V_{GS} = 0\text{ V}, T_J = 55\text{ }^\circ\text{C}$	P-Ch			-5		
On-State Drain Current ^b	$I_{D(on)}$	$V_{DS} = 5\text{ V}, V_{GS} = 10\text{ V}$	N-Ch	30			A	
		$V_{DS} = -5\text{ V}, V_{GS} = -4.5\text{ V}$	P-Ch	-20				
Drain-Source On-State Resistance ^b	$R_{DS(on)}$	$V_{GS} = 10\text{ V}, I_D = 8.8\text{ A}$	N-Ch		0.015	0.018	Ω	
		$V_{GS} = -4.5\text{ V}, I_D = -5.7\text{ A}$	P-Ch		0.030	0.042		
		$V_{GS} = 4.5\text{ V}, I_D = 7.0\text{ A}$	N-Ch		0.022	0.027		
		$V_{GS} = -2.5\text{ V}, I_D = -4.8\text{ A}$	P-Ch		0.048	0.060		
Forward Transconductance ^b	g_{fs}	$V_{DS} = 15\text{ V}, I_D = 8.8\text{ A}$	N-Ch		18		S	
		$V_{DS} = -15\text{ V}, I_D = -5.7\text{ A}$	P-Ch		12			
Diode Forward Voltage ^b	V_{SD}	$I_S = 1.8\text{ A}, V_{GS} = 0\text{ V}$	N-Ch		0.73	1.1	V	
		$I_S = -1.8\text{ A}, V_{GS} = 0\text{ V}$	P-Ch		-0.75	-1.1		
Dynamic^a								
Total Gate Charge	Q_g	N-Channel $V_{DS} = 15\text{ V}, V_{GS} = 5\text{ V}, I_D = 8.8\text{ A}$	N-Ch		11.5	20	nC	
			P-Ch		13.5	20		
Gate-Source Charge	Q_{gs}	P-Channel $V_{DS} = -4\text{ V}, V_{GS} = -5\text{ V}, I_D = -5.7\text{ A}$	N-Ch		3		nC	
			P-Ch		2.2			
Gate-Drain Charge	Q_{gd}	N-Channel $V_{DS} = -4\text{ V}, V_{GS} = -5\text{ V}, I_D = -5.7\text{ A}$	N-Ch		4		nC	
			P-Ch		3			
Turn-On Delay Time	$t_{d(on)}$	N-Channel $V_{DD} = 15\text{ V}, R_L = 15\text{ }\Omega$ $I_D \cong 1\text{ A}, V_{GEN} = 10\text{ V}, R_G = 6\text{ }\Omega$	N-Ch		15	22	ns	
Rise Time	t_r		P-Ch		21	40		
		Turn-Off Delay Time	$t_{d(off)}$	N-Ch		8		15
Fall Time	t_f			P-Ch		45		70
		Source-Drain Reverse Recovery Time	t_{rr}	P-Channel $V_{DD} = -4\text{ V}, R_L = 4\text{ }\Omega$ $I_D \cong -1\text{ A}, V_{GEN} = -4.5\text{ V}, R_g = 6\text{ }\Omega$	N-Ch			35
P-Ch					60	100		
Source-Drain Reverse Recovery Time	t_{rr}	N-Channel $I_F = 1.8\text{ A}, di/dt = 100\text{ A}/\mu\text{s}$	N-Ch		10	20		ns
			P-Ch		55	85		
Source-Drain Reverse Recovery Time	t_{rr}	P-Channel $I_F = 1.8\text{ A}, di/dt = 100\text{ A}/\mu\text{s}$	N-Ch		30	60	ns	
			P-Ch		50	100		

Notes:

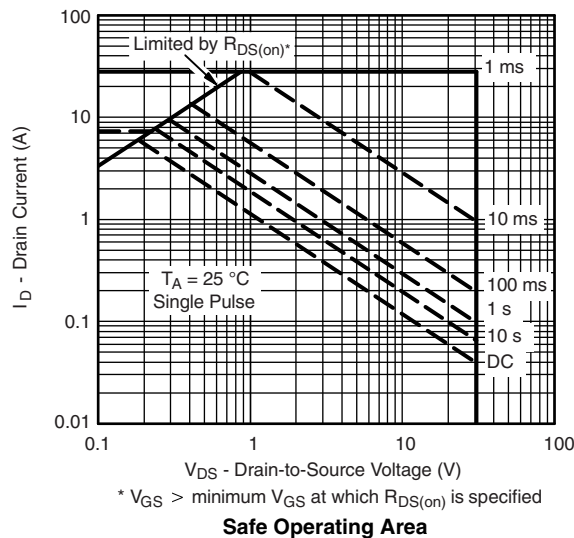
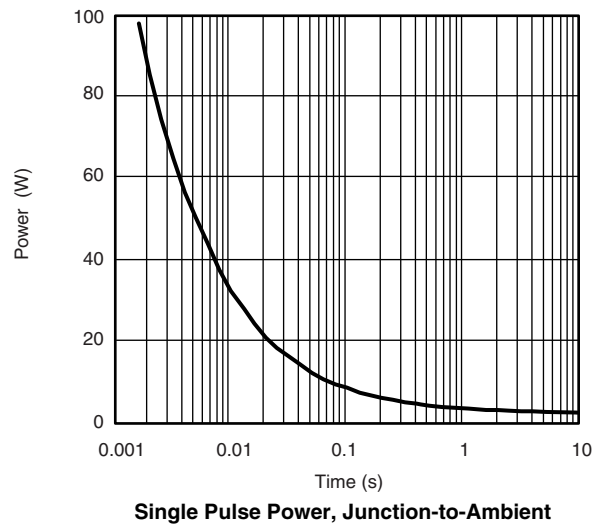
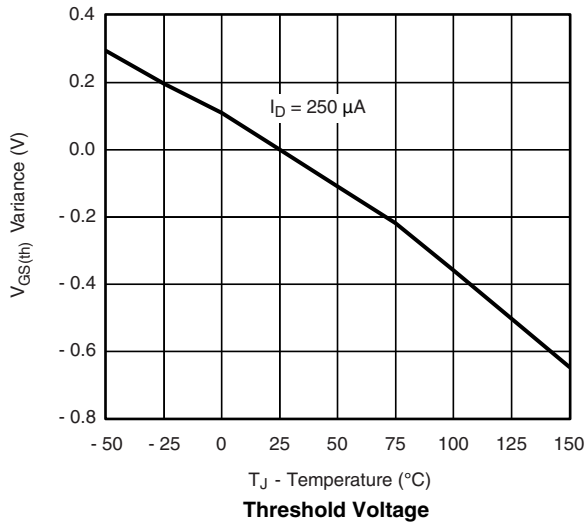
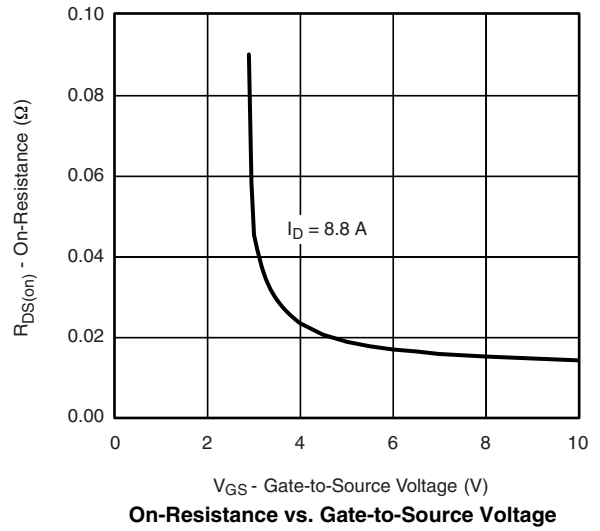
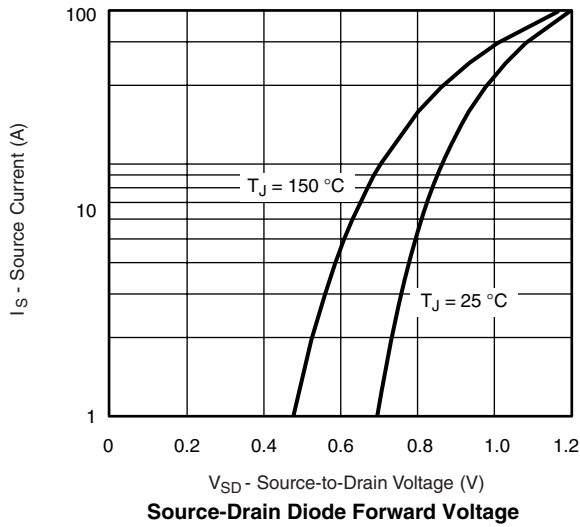
- a. Guaranteed by design, not subject to production testing.
b. Pulse test; pulse width $\leq 300\text{ }\mu\text{s}$, duty cycle $\leq 2\%$.

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

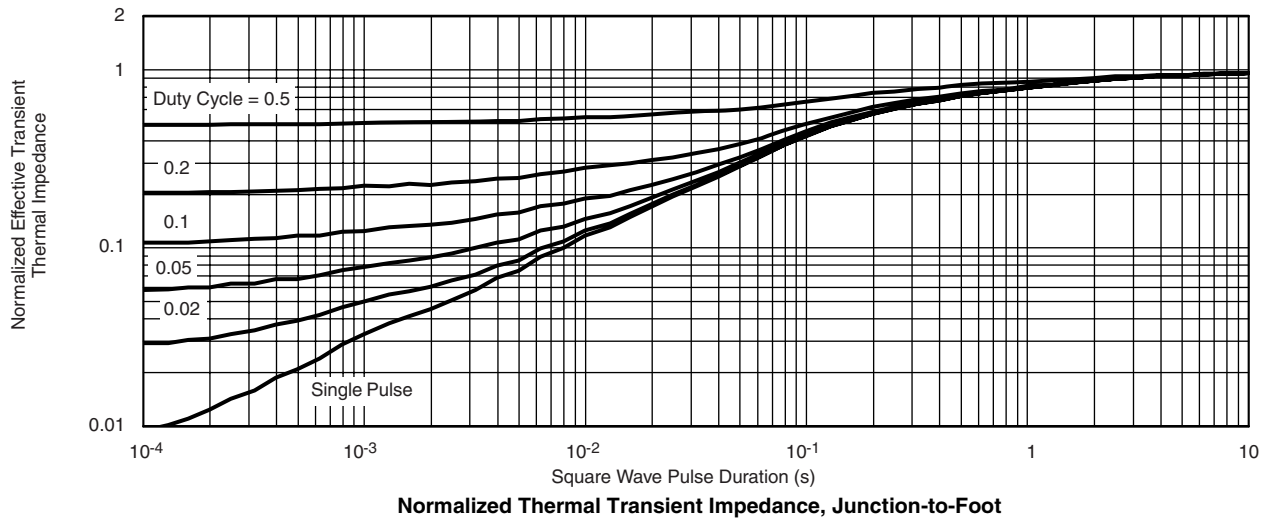
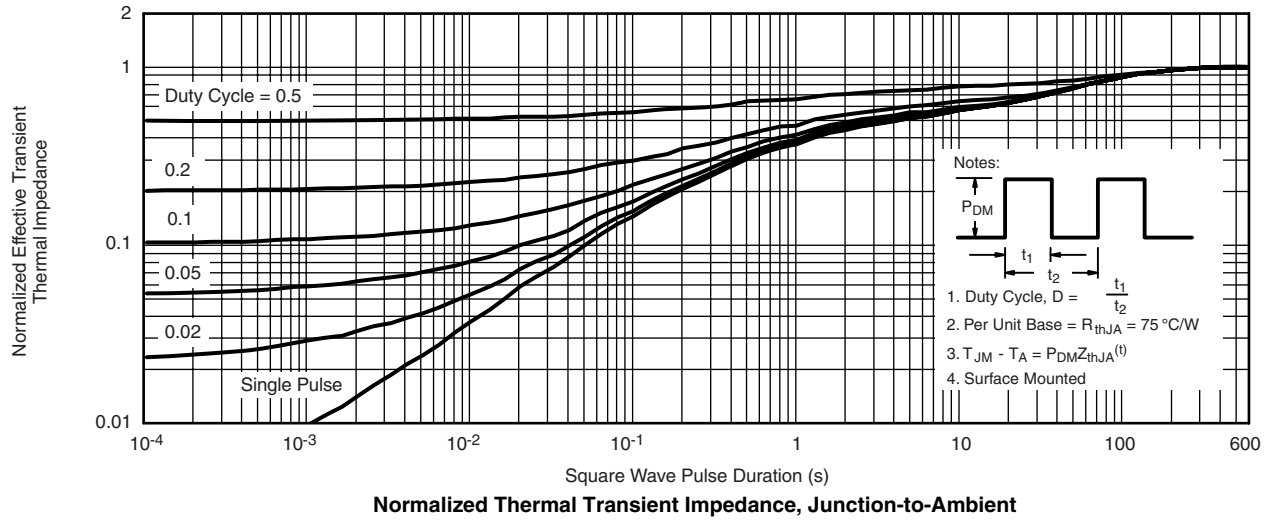
N-CHANNEL TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted



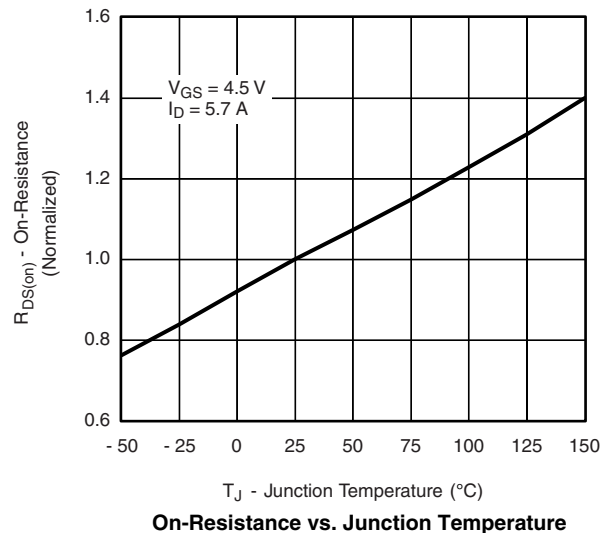
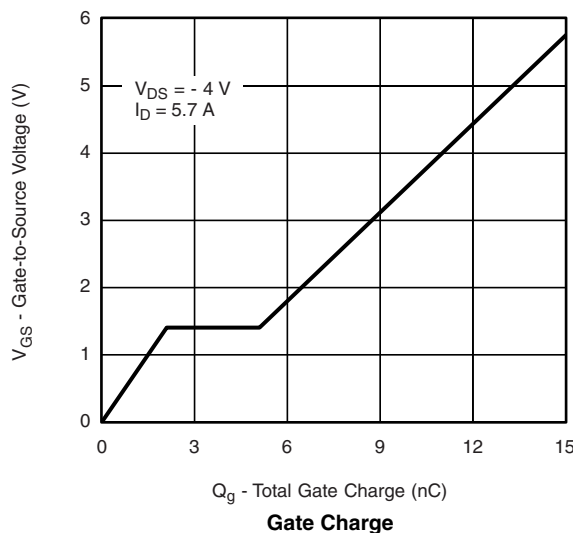
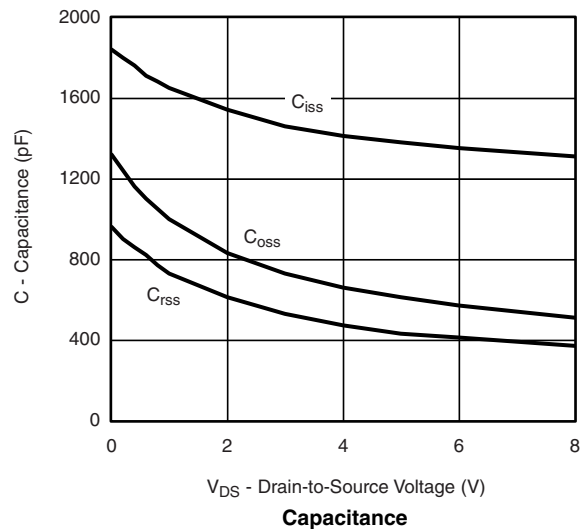
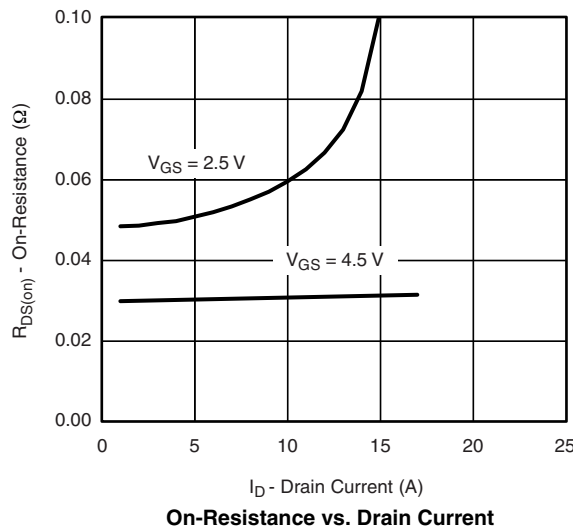
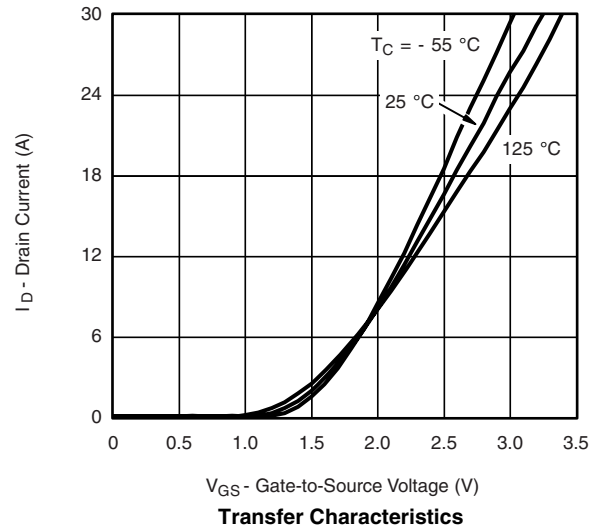
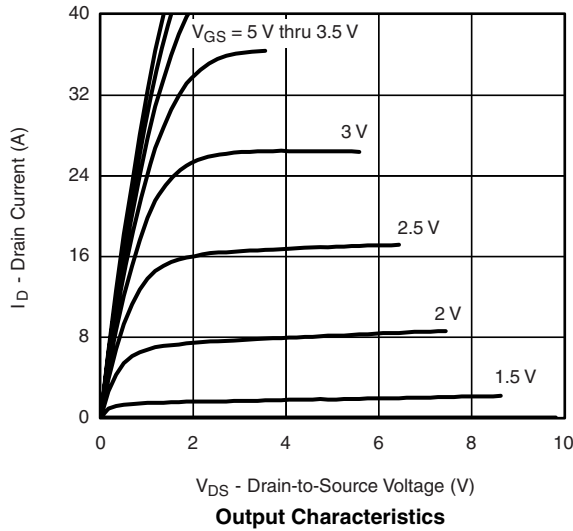
N-CHANNEL TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted



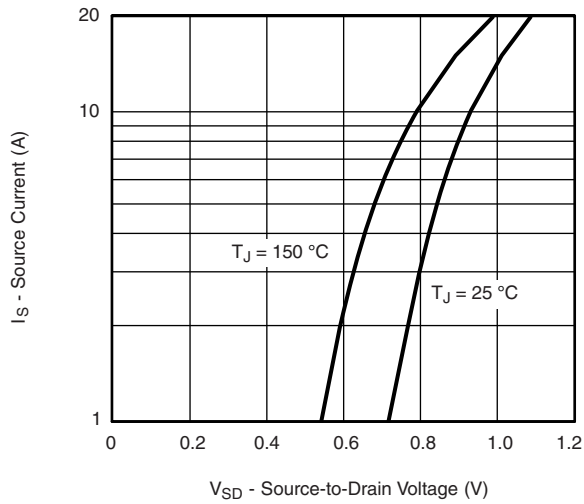
N-CHANNEL TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted



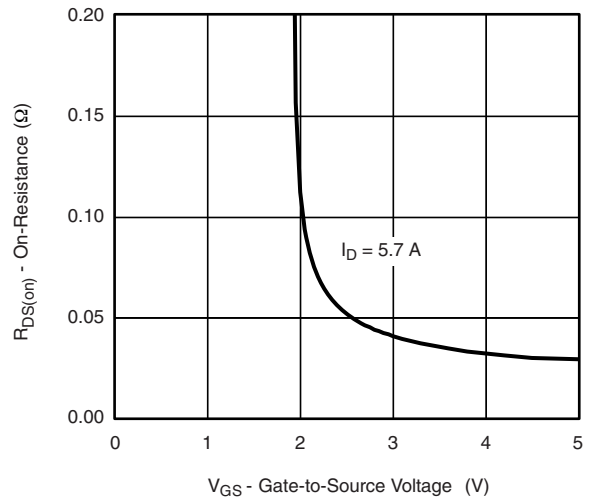
P-CHANNEL TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted



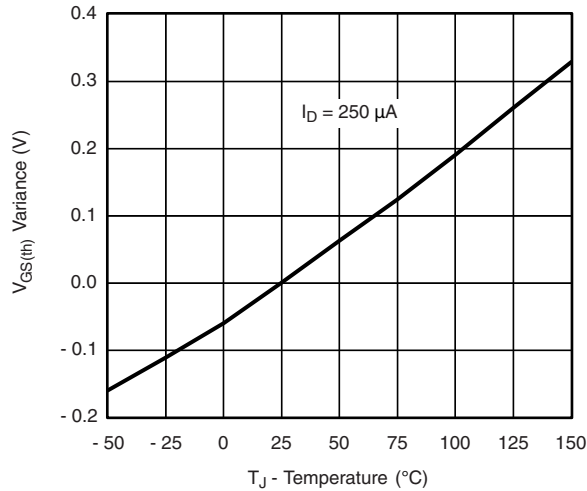
P-CHANNEL TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted



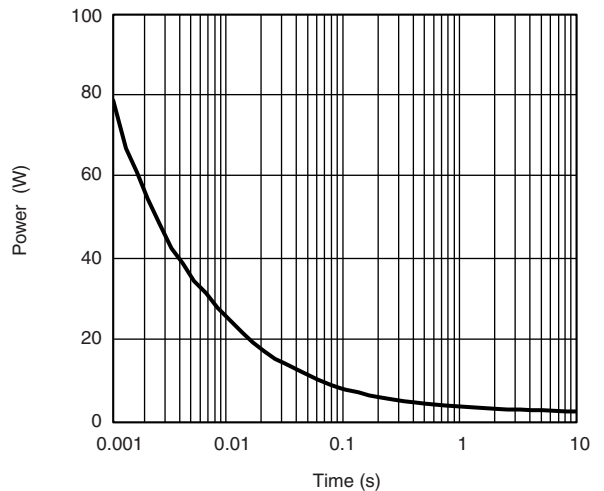
Source-Drain Diode Forward Voltage



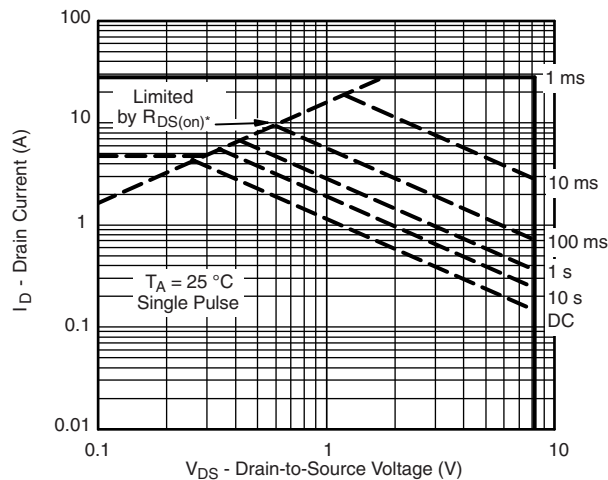
On-Resistance vs. Gate-to-Source Voltage



Threshold Voltage



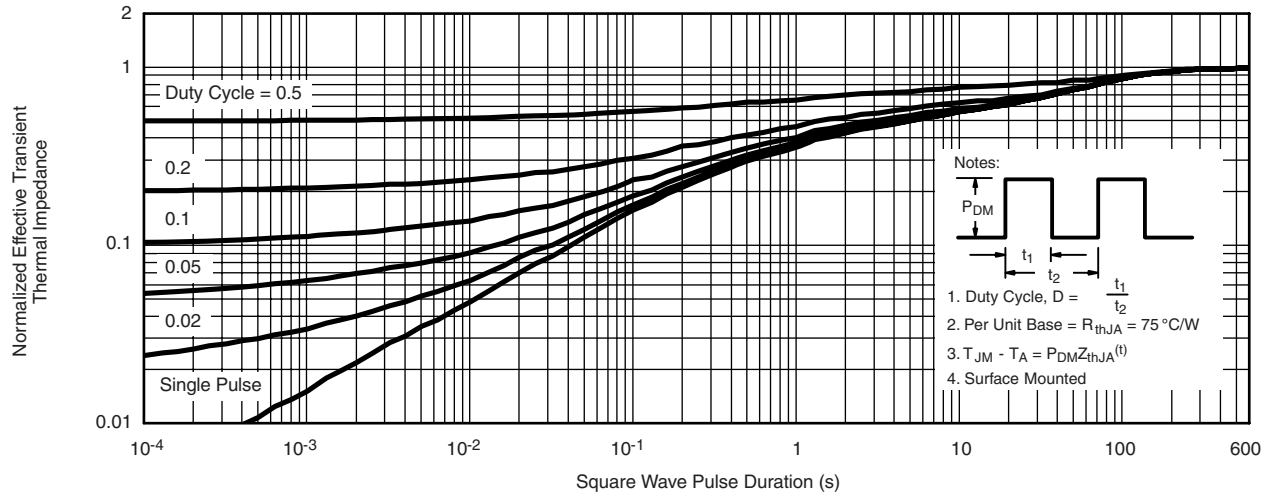
Single Pulse Power, Junction-to-Ambient



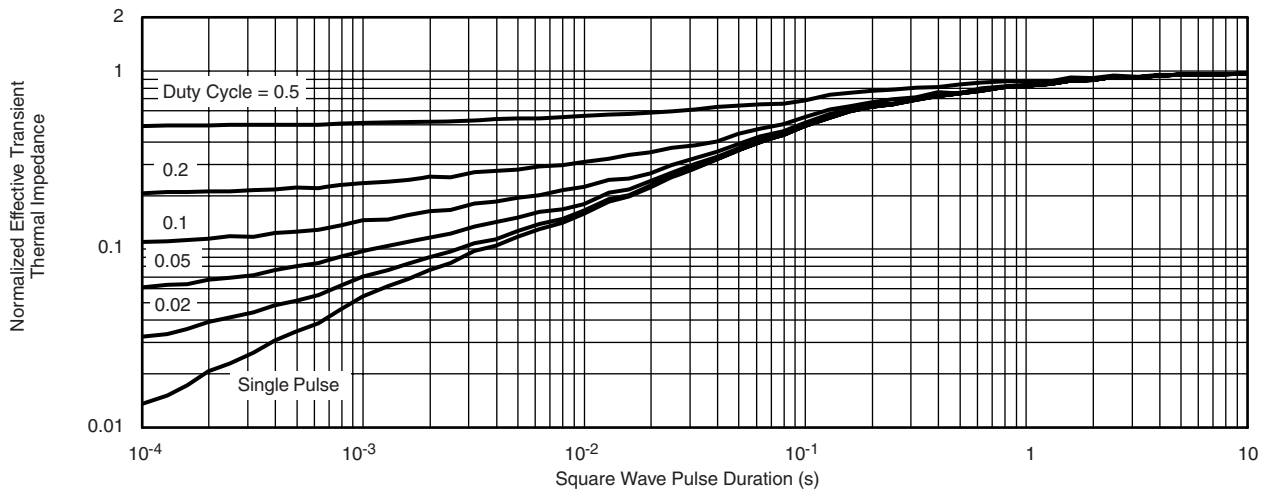
* $V_{GS} >$ minimum V_{GS} at which $R_{DS(on)}$ is specified

Safe Operating Area

P-CHANNEL TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted



Normalized Thermal Transient Impedance, Junction-to-Ambient



Normalized Thermal Transient Impedance, Junction-to-Foot

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